

Please add the following new claims:

-- 32. The wiring according to claim 2, wherein said metallic alloy film is an alloy film of one element, or a plurality of elements, selected from the group consisting of Ta; Ti; Mo; Cr; Nb; and Si, and tungsten. --

-- 33. The wiring according to claim 2, wherein said metallic compound film is a nitride film of tungsten.--

9 34. The semiconductor device according to claim 7, wherein said wiring is a gate wiring of a thin film transistor.--

-- 35. The semiconductor device according to claim 7, wherein said semiconductor device is an active matrix type liquid crystal display device. --

-- 36. The semiconductor device according to claim 7, wherein said semiconductor device is an EL display device.--

-- 37. The semiconductor device according to claim 7, wherein said semiconductor device is one selected from the group consisting of a video camera, a digital camera, a projector, a goggle type display, a car navigation system, a personal computer, or a portable information terminal. --

-- 38. The method of forming a wiring according to claim 17, wherein said etching is performed using an etching gas comprising a mixed gas of a first reaction gas containing fluorine and a second reaction gas containing chlorine, and a specific selectivity in said etching gas between said base film and said metallic thin film is 2.5 or more. --

-- 39. The method of forming a wiring according to claim 17, wherein said metallic thin film is a thin film, or a laminated film of thin films, selected from the group consisting of: tungsten film; a metallic compound film having a tungsten compound film as its main constituent; and a metallic alloy film having a tungsten alloy as its main constituent. --